# **TN0702**

## N-Channel Enhancement-Mode Vertical DMOS FET

#### **Features**

- · 1.6V Maximum Low Threshold
- · High Input Impedance
- 130 pF Typical Low Input Capacitance
- · Fast Switching Speeds
- · Low On-Resistance Guaranteed at  $V_{GS}$  = 2V, 3V and 5V
- · Free from Secondary Breakdown
- · Low Input and Output Leakage

#### **Applications**

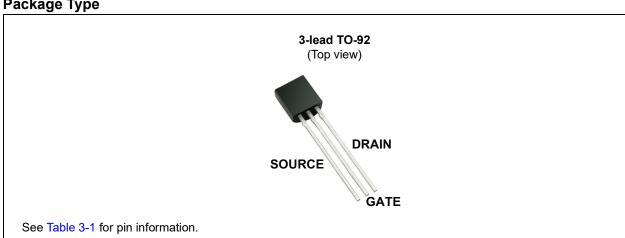
- Logic-Level Interfaces (Ideal for TTL and CMOS)
- · Solid-State Relays
- · Battery-Operated Systems
- · Photovoltaic Drives
- · Analog Switches
- · General Purpose Line Drivers
- · Telecommunication Switches

#### **General Description**

TN0702 low-threshold Enhancement-mode (normally-off) transistor uses a vertical DMOS structure and a well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally induced secondary breakdown.

Microchip's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

#### **Package Type**



#### 1.0 ELECTRICAL CHARACTERISTICS

#### **Absolute Maximum Ratings†**

Drain-to-Source Voltage	BV <sub>DSS</sub>
Drain-to-Gate Voltage	
Gate-to-Source Voltage	
Operating Ambient Temperature, T <sub>A</sub>	
Storage Temperature, T <sub>S</sub>	

**† Notice:** Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

#### DC ELECTRICAL CHARACTERISTICS

**Electrical Specifications:**  $T_A = 25^{\circ}$ C unless otherwise specified. All DC parameters are 100% tested at 25°C unless otherwise stated. (Pulse test: 300 µs pulse, 2% duty cycle)

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Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions			
Drain-to-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS}$ = 0V, $I_D$ = 1 mA			
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	0.8	1	V	$V_{GS} = V_{DS}$ , $I_D = 1 \text{ mA}$			
Change in V <sub>GS(th)</sub> with Temperature	$\Delta V_{GS(th)}$			-4	mV/°C	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 1 mA ( <b>Note 1</b> )			
Gate Body Leakage Current	I <sub>GSS</sub>	_		100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$			
				100	nA	V <sub>GS</sub> = 0V, V <sub>DS</sub> = Maximum rating			
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>			100	μΑ	$V_{DS}$ = 0.8 Maximum rating, $V_{GS}$ = 0V, $T_A$ = 125°C (Note 1)			
On-State Drain Current	I <sub>D(ON)</sub>	0.5	1		Α	$V_{GS} = V_{DS} = 5V$			
		_	4	5	Ω	$V_{GS}$ = 2V, $I_D$ = 50 mA			
Static Drain-to-Source On-State Resistance	R <sub>DS(ON)</sub>	_	1.9	2.5	Ω	$V_{GS} = 3V, I_{D} = 200 \text{ mA}$			
	, ,	_	1	1.3	Ω	$V_{GS} = 5V, I_D = 500 \text{ mA}$			
Change in R <sub>DS(ON)</sub> with Temperature	ΔR <sub>DS(ON)</sub>			0.75	%/°C	V <sub>GS</sub> = 5V, I <sub>D</sub> = 500 mA ( <b>Note 1</b> )			

**Note 1:** Specification is obtained by characterization and is not 100% tested.

## **AC ELECTRICAL CHARACTERISTICS**

Electrical Specifications: T <sub>A</sub> = 25°C unless otherwise specified. All AC parameters are sample tested.								
Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions		
Forward Transconductance	G <sub>FS</sub>	100	500	_	mmho	$V_{DS} = 5V, I_{D} = 500 \text{ mA}$		
Input Capacitance	C <sub>ISS</sub>	_	130	200	рF	V <sub>GS</sub> = 0V,		
Common-Source Output Capacitance		_	70	125	рF	V <sub>DS</sub> = 20V,		
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	30	60	рF	f = 1 MHz		
Turn-On Delay Time		_	1	20	ns			
Rise Time		_		20	ns	$V_{DD} = 20V,$		
Turn-Off Delay Time		_	_	30	ns	$I_D = 0.5A,$ $R_{GEN} = 25\Omega$		
Fall Time		_	_	20	ns	- GEN		
DIODE PARAMETER								
Diode Forward Voltage Drop	$V_{SD}$	_	_	1	V	V <sub>GS</sub> = 0V, I <sub>SD</sub> = 0.5A ( <b>Note 1</b> )		

Note 1: All DC parameters are 100% tested at 25°C unless otherwise stated. (Pulse test: 300 µs pulse, 2% duty cycle)

### **TEMPERATURE SPECIFICATIONS**

Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions	
TEMPERATURE RANGE							
Operating Ambient Temperature	T <sub>A</sub>	-55	_	+150	°C		
Storage Temperature	T <sub>S</sub>	-55	_	+150	°C		
PACKAGE THERMAL RESISTANCE							
3-lead TO-92			132	_	°C/W		

### THERMAL CHARACTERISTICS

Package	I <sub>D</sub> (Note 1) (Continuous) (mA)	I <sub>D</sub> (Pulsed) (A)	Power Dissipation at T <sub>A</sub> = 25°C (W)	I <sub>DR</sub> (Note 1) (mA)	I <sub>DRM</sub> (A)
3-lead TO-92	530	1	1	530	1

**Note 1:**  $I_D$  (continuous) is limited by maximum rated  $T_J$ .

#### 2.0 TYPICAL PERFORMANCE CURVES

**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g. outside specified power supply range) and therefore outside the warranted range.

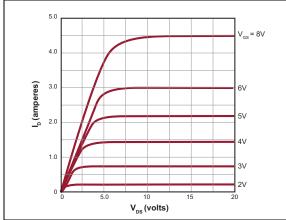


FIGURE 2-1: Output Characteristics.

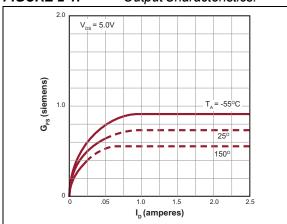
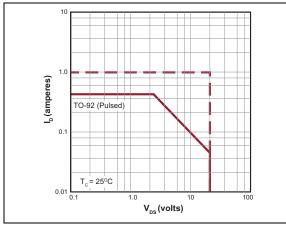


FIGURE 2-2: Transconductance vs. Drain Current.



**FIGURE 2-3:** Maximum Rated Safe Operating Area.

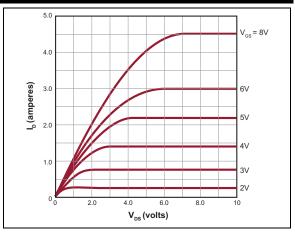
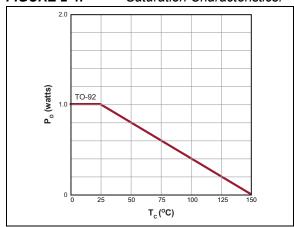
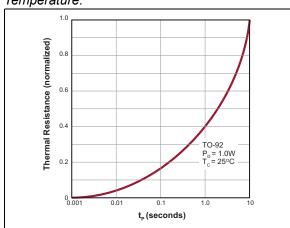


FIGURE 2-4: Saturation Characteristics.



**FIGURE 2-5:** Power Dissipation vs. Case Temperature.



**FIGURE 2-6:** Thermal Response Characteristics.

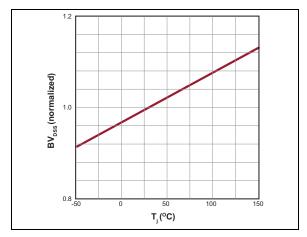


FIGURE 2-7: Temperature.

 $BV_{DSS}$  Variation with

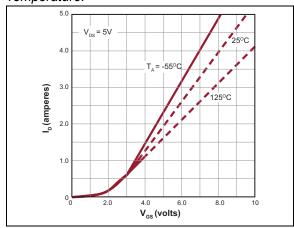
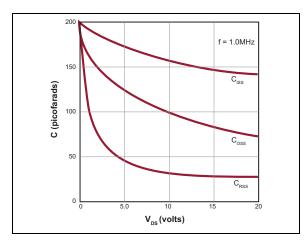


FIGURE 2-8:

Transfer Characteristics.



**FIGURE 2-9:** Capacitance vs. Drain-to-Source Voltage.

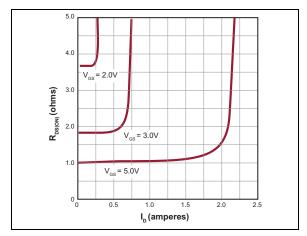


FIGURE 2-10: Current.

On-Resistance vs. Drain

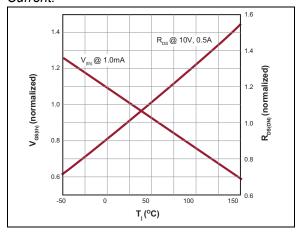


FIGURE 2-11: with Temperature.

 $V_{GS(th)}$  and  $R_{DS}$  Variation

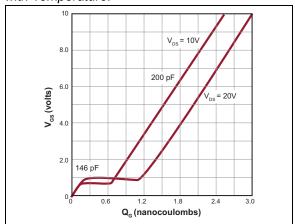


FIGURE 2-12: Characteristics.

Gate Drive Dynamic

## TN0702

### 3.0 PIN DESCRIPTION

Table 3-1 shows the description of pins in TN0702. Refer to **Package Type** for the location of pins.

#### TABLE 3-1: PIN FUNCTION TABLE

Pin Number	Pin Name	Description
1	Source	Source
2	Gate	Gate
3	Drain	Drain

### 4.0 FUNCTIONAL DESCRIPTION

Figure 4-1 illustrates the switching waveforms and test circuit for TN0702.

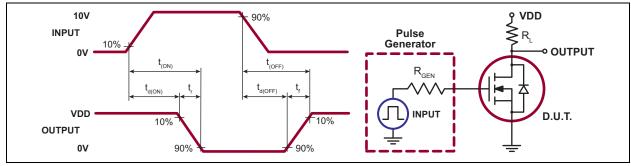


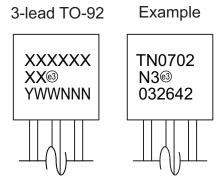
FIGURE 4-1: Switching Waveforms and Test Circuit.

TABLE 4-1: PRODUCT SUMMARY

BV <sub>DSS</sub> /BV <sub>DGS</sub> (V)	R <sub>DS(ON)</sub>	I <sub>D(ON)</sub>	V <sub>GS(th)</sub>
	(Maximum)	(Minimum)	(Maximum)
	(Ω)	(A)	(V)
20	1.3	0.5	1

#### 5.0 PACKAGING INFORMATION

### 5.1 Package Marking Information

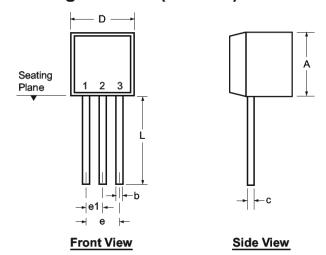


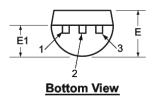
Legend: XX...X Product Code or Customer-specific information
Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')
NNN Alphanumeric traceability code

(e3 Pb-free JEDEC® designator for Matte Tin (Sn)
\* This package is Pb-free. The Pb-free JEDEC designator (e3)
can be found on the outer packaging for this package.

**Note**: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for product code or customer-specific information. Package may or not include the corporate logo.

## 3-Lead TO-92 Package Outline (L/LL/N3)





Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

Symb	ool	Α	b	С	D	Е	E1	е	e1	L
	MIN	.170	.014 <sup>†</sup>	.014 <sup>†</sup>	.175	.125	.080	.095	.045	.500
Dimensions (inches)	NOM	-	-	-	-	-	-	-	-	-
()	MAX	.210	.022 <sup>†</sup>	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.
\* This dimension is not specified in the JEDEC drawing.
† This dimension differs from the JEDEC drawing.

Drawings not to scale.

## TN0702

**NOTES:** 

### APPENDIX A: REVISION HISTORY

### **Revision A (September 2020)**

- Converted Supertex Doc# DSFP-TN0702 to Microchip DS20005941A
- Changed the package marking format
- Removed the TO-92 N3 P002, P003, P005, P013, and P014 media types to align package specifications with the actual BQM
- Made minor text changes throughout the document

## PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

PART NO.	<u> </u>		- <u>x</u> - <u>x</u>	Example:
Device	Packa Optio		Environmental Media Type	a) TN0702N3-G:  N-Channel Enhancement- Mode, Vertical DMOS FET, 3-lead TO-92,1000/Bag
Device:	TN0702	=	N-Channel Enhancement-Mode Vertical DMOS FET	
Package:	N3	=	3-lead TO-92	
Environmental:	G	=	Lead (Pb)-free/RoHS-compliant Package	
Media Type:	(blank)	=	1000/Bag for an N3 Package	

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